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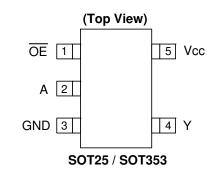
Description

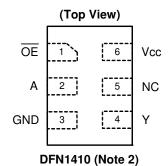
The 74LVCE1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output enable (OE) pin. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

Features

- Extended Supply Voltage Range from 1.4 to 5.5V
- · Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
 Exceeds 200-V Machine Model (A115-A)
 Exceeds 2000-V Human Body Model (A114-A)
 - Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- SOT25, SOT353 and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

Pin Assignments





Applications

- Voltage Level Shifting
- Bus Driver / Repeater
- Power Down Signal Isolation
- · General Purpose Logic
- Wide array of products such as.
 - o PCs, networking, notebooks, netbooks, PDAs
 - o Computer peripherals, hard drives, CD/DVD ROM
 - o TV, DVD, DVR, set top box
 - o Cell Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

2. Pin 2 and pin 5 of the DFN1410 package are internally connected.

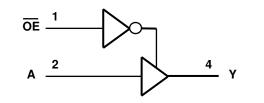


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Pin Descriptions

Pin Name	Description
ŌĒ	Output Enable (active low)
А	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage

Logic Diagram



Function Table

Inp	Output	
ŌĒ	Y	
L	Н	Н
L	L	L
Н	Х	Z



Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
Ι _{οκ}	Output Clamp Current	-50	mA
Ι _Ο	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

74LVCE1G125 Document number: DS32216 Rev. 2 - 2



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Recommended Operating Conditions (Note 4)

Symbol		Parameter	Min	Max	Unit	
V	Oneveting Veltage	Operating	1.4	5.5	V	
V_{CC}	Operating Voltage	Data retention only	1.2		V	
		$V_{\rm CC} = 1.4$ V to 1.95 V	0.65 X V _{CC}			
V		$V_{\rm CC} = 2.3 \text{ V}$ to 2.7 V	1.7		v	
V _{IH}	V _{IH} High-level Input Voltage	V _{CC} = 3 V to 3.6 V	2		v	
		$V_{CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	0.7 X V _{CC}			
		V _{CC} = 1.4 V to 1.95 V		0.35 X V_{CC}		
V		$V_{\rm CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$		0.7	v	
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	v	
		$V_{\rm CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$		0.3 X V _{CC}		
VI	Input Voltage	•	0	5.5	V	
Vo	Output Voltage		0	V _{cc}	V	
		Vcc=1.4 V		-3		
		V _{CC} = 1.65 V		-4		
	I link laval autout aumout	$V_{\rm CC} = 2.3 \rm V$		-8		
I _{OH}	High-level output current			-16	mA	
		$V_{CC} = 3 V$		-24		
		$V_{\rm CC} = 4.5 \rm V$		-32		
		Vcc=1.4 V		3		
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8	mA	
I _{OL}	Low-level output current			16		
		$V_{CC} = 3 V$		24		
		$V_{\rm CC} = 4.5 V$		32		
		$V_{\rm CC} = 1.4$ to 3V		20		
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
	rate	$V_{CC} = 5 V \pm 0.5 V$		5		
T _A	Operating free-air temperature		-40	85	⁰C	

Note: 4. Unused inputs should be held at Vcc or Ground.





Electrical Characteristics (All typical values are at Vcc = 3.3V, T_A = 25°C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit
-		I _{OH} = -100μA	1.4 V to 5.5V	$V_{CC} - 0.1$			
		I _{OH} = -3mA	1.4 V	1.05			
		I _{OH} = -4mA	1.65 V	1.2			
V _{OH}	High Level Output Voltage	I _{OH} = -8mA	2.3V	1.9			V
	Vollage	I _{OH} = -16mA	2.1/	2.4			
		I _{OH} = -24mA	3 V	2.3			
		I _{OH} = -32mA	4.5 V	3.8			
		$I_{OL} = 100 \mu A$	1.4 V to 5.5V			0.1	
		$I_{OL} = 3mA$	1.4V			.4	
		$I_{OL} = 4mA$	1.65 V			0.45	
V_{OL}	Y _{OL} High-level Input Voltage	$I_{OL} = 8mA$	2.3V			0.3	V
		$I_{OL} = 16 \text{mA}$	3 V			0.4	
		$I_{OL} = 24 \text{mA}$	5 V			0.55	
		$I_{OL} = 32mA$	4.5			0.55	
I _I	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μA
I _{OFF}	Power Down Leakage Current	$V_1 \text{ or } V_0 = 5.5 V$	0			± 10	μA
I _{OZ}	Z State Leakage Current	$V_0 = 0$ to 5.5V	3.6V			10	μA
I _{CC}	Supply Current	$V_1 = 5.5V \text{ of GND}$ $I_0=0$	1.4 V to 5.5V			10	μA
ΔI_{CC}	Additional Supply Current	One input at V_{CC} – 0.6 V Other inputs at V_{CC} or GND	3 V to 5.5V			500	μA
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		3.5		pF
	The second Decision of	SOT25	(Note 5)		204		
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5)		371		°C/W
		DFN1410	(Note 5)		430		
	The secol Decision	SOT25	(Note 5)		52		
θ_{JC}	Thermal Resistance Junction-to-Case	SOT353	(Note 5)		143		°C/W
		DFN1410	(Note 5)		190]

Note: 5. Test condition for SOT25, SOT353 and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Switching Characteristics

Parameter	From (Input)	-	-	-	-	то	± 0.					Vcc = 2.5 V ± 0.2V		Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V	
		ut) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Мах	Min	Мах	Unit				
t _{pd}	А	Y	1.9	6.9	1.3	4.8	0.5	3.6	0.4	3	0.4	3	ns				

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From	то	Vcc = ± 0			: 1.8 V .15V		: 2.5 V).2V		: 3.3 V).3V		= 5 V).5V	Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	•
t _{pd}	А	Y	2.8	9	1.9	6.3	0.9	4.4	0.8	3.6	0.9	3.6	ns
t _{en}	ŌĒ	Y	3.3	10.1	2.3	7	1.2	5.2	0.8	4.3	0.9	4.5	
t _{dis}	ŌĒ	Y	1.3	9.2	0.9	6.4	0.8	4	0.8	4.1	0.9	3.7	

Operating Characteristics

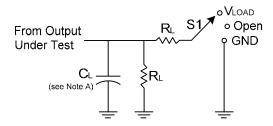
 $T_A = 25 \ ^{o}C$

	Paramete	er	Test Conditions		Vcc = 1.8 V TYP	Vcc = 2.5 V TYP	Vcc = 3.3 V TYP	Vcc = 5 V TYP	Unit
6	Power	Outputs enabled	f 10 MU-	20	20	20	21	22	۳E
C _{pd}	dissipation capacitance	Outputs disabled	f = 10 MHz	2	2	2	2	4	pF



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information

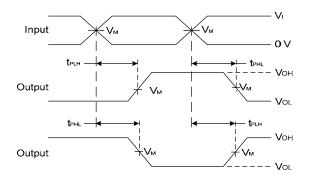


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

Vcc	In	puts	N _e	C	RL
VCC	VI	t _r /t _f	₩	V _M C _L	
1.5V±0.1V	V _{CC}	≤2ns	V _{CC} /2	15pF	1MΩ
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	15pF	1MΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	15pF	1MΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1MΩ
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	15pF	1MΩ



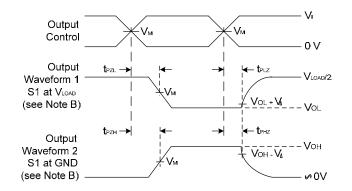
Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as t_{dis.}
 - E. t_{PZL} and t_{PZH} are the same as $t_{\text{EN.}}$
 - F. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$

Figure 1. Load Circuit and Voltage Waveforms

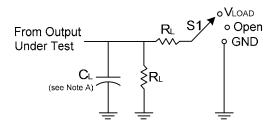


Voltage Waveform Enable and Disable Times Low and High Level Enabling



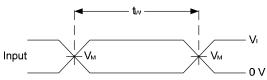
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information (Continued)

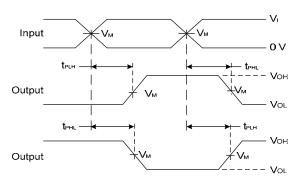


TEST	S1
-	-
t _{PLH} /t _{PHL}	Open
1 /1	Vlaad
t _{PLZ} /t _{PZL}	Vload
+ /+	GND
t _{PHZ} /t _{PZH}	GND

Vcc	Ing	outs	V _M	CL	RL
	Vi	t _r /t _f	• 111	υĽ	
1.5V±0.1V	V _{CC}	≤2ns	V _{CC} /2	30pF	1KΩ
1.8V±0.15V	V _{CC}	≤2ns	V _{CC} /2	30pF	1KΩ
2.5V±0.2V	V _{CC}	≤2ns	V _{CC} /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V _{CC}	≤2.5ns	V _{CC} /2	50pF	500Ω



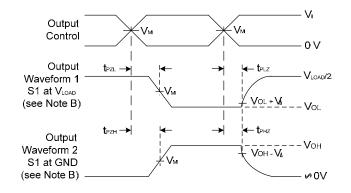
Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
 - E. t_{PZL} and t_{PZH} are the same as t_{EN0}
 - F. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$

Figure 2. Load Circuit and Voltage Waveforms

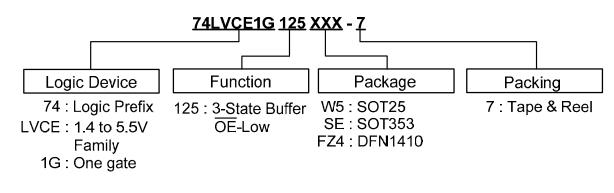


Voltage Waveform Enable and Disable Times Low and High Level Enabling



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Ordering Information



Device	Package	Packaging (Note 5)	7" Tape and Reel	
Device	Code		Quantity	Part Number Suffix
74LVCE1G125W5-7	W6	SOT25	3000/Tape & Reel	-7
74LVCE1G125SE-7	SE	SOT353	3000/Tape & Reel	-7
74LVCE1G125FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

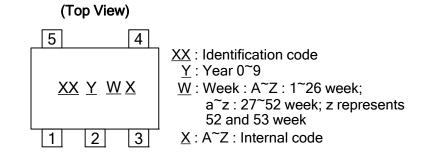
Note: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Marking Information

(1) SOT25 and SOT353



Part Number	Package	Identification Code
74LVCE1G125W5	SOT25	PY
74LVCE1G125SE	SOT353	PY

(2) DFN1410

(Top View)



 $\underline{XX} : \text{Identification Code} \\ \underline{Y} : \text{Year} : 0~9 \\ \underline{W} : \text{Week} : A~Z : 1~26 \text{ week}; \\ a~z : 27~52 \text{ week}; z \text{ represents} \\ 52 \text{ and } 53 \text{ week} \\ \underline{X} : A~Z : \text{Internal code} \\ \end{bmatrix}$

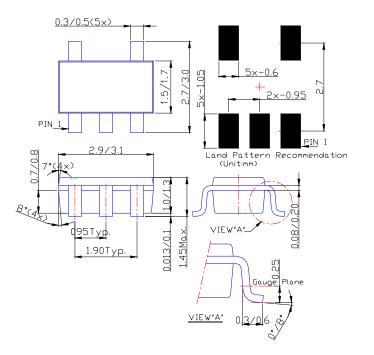
Part Number	Package	Identification Code
74LVCE1G125FZ4	DFN1410	PY



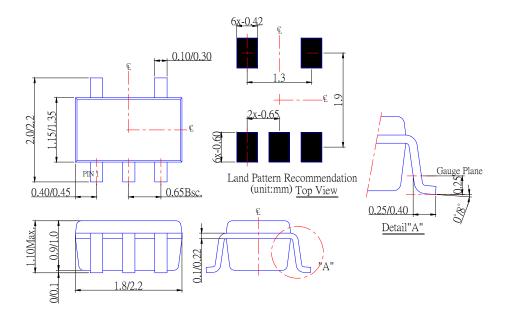
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



(2) Package Type: SOT353



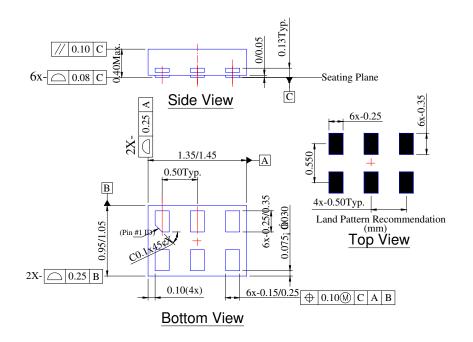
74LVCE1G125 Document number: DS32216 Rev. 2 - 2



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Package Outline Dimensions (All Dimensions in mm)

(3) Package Type: DFN1410

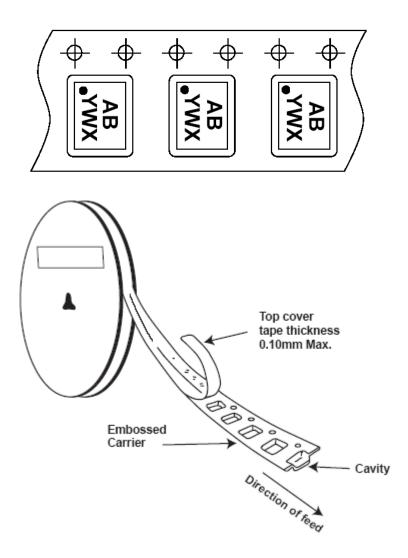




SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Taping Orientation (Note 7)

For DFN1410







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